

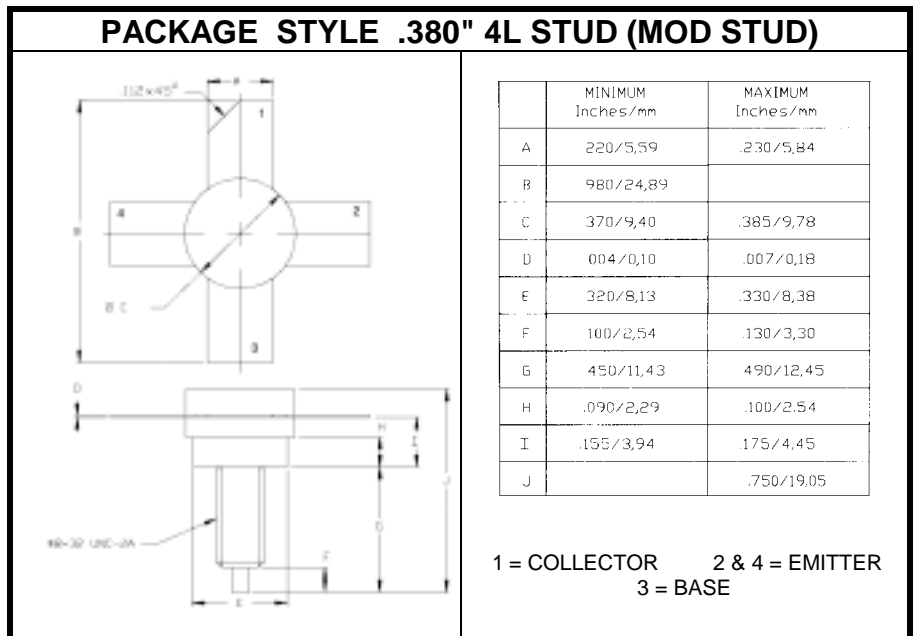
NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW75** is Designed for 25V Large-Signal Amplifier Applications, TV Transposers, and Transmitters Operating in Band III.

MAXIMUM RATINGS

I_C	4.0 A
V_{CE}	32 V
V_{CB}	60 V
P_{DISS}	60 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +125 °C
θ_{JC}	1.9 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CER}	I _C = 50 mA	R _{BE} = 10 Ω	60			V
BV_{CBO}	I _C = 50 mA		60			V
BV_{CEO}	I _C = 50 mA		30			V
BV_{EBO}	I _E = 10 mA		4.0			V
h_{FE}	V _{CE} = 25 V	I _C = 2.0 A	20	45		---
C_{ob}	V _{CB} = 30 V			90	120	pF
		f = 1.0 MHz				
C_{re}	V _{CE} = 30 V	I _C = 200 mA		55		pF
		f = 1.0 MHz				
f_T	V _{CE} = 25 V	I _C = 6.0 A		800		MHz
		f = 100 MHz				